

ME2807



Voltage Detectors, ME2807 Series

General Description

ME2807 Series are a set of three-terminal low power voltage detectors implemented in CMOS technology. Each voltage detector in the series detects a particular fixed voltage ranging from 2.0V to 7.0V. The voltage detectors consist of a high precision and low power consumption standard voltage source, a comparator, hysteresis circuit, and an output driver. CMOS technology ensures low power consumption.

Features

- Highly accuracy Detection voltage: ± 1%
- Low power consumption: TYP 1.8uA (Vin=3V)
- Detection voltage range: 2.0V~7.0V in 0.1V increments
- Operating voltage range: 1.5V~18V
- Detect voltage temperature characteristics:
 TYP ± 0.9mV/°C
- Output configuration: CMOS

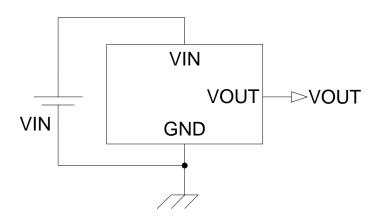
Typical Application

- battery checkers
- Level selectors
- Power failure detectors
- Microcomputer reset
- Battery backup of Memories
- Store non-volatile RAM signal protectors

Package

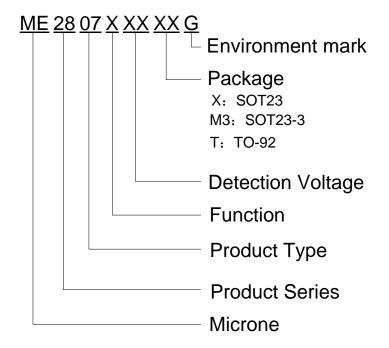
• 3-pin SOT23、SOT23-3、TO-92

Typical Application Circuit





Selection Guide



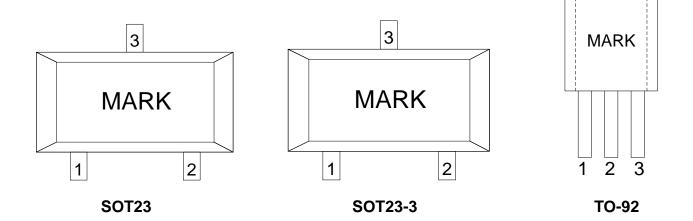
product series	product description			
ME2807A27XG	VIN=H→ L V _{DET} =2.7V; VIN Falling edge detection; Package: SOT23			
ME2807A33XG	VIN=H→ L V _{DET} =3.3V; VIN Falling edge detection; Package: SOT23			
ME2807A22M3G	VIN=H→ L V _{DET} =2.2V; VIN Falling edge detection; Package: SOT23-3			
ME2807A33M3G	VIN=H→ L V _{DET} =3.3V; VIN Falling edge detection; Package: SOT23-3			
ME2807A22TG	VIN=H→ L V _{DET} =2.2V; VIN Falling edge detection; Package: TO-92			
ME2807B33M3G	VIN=L→ H V _{DET} =3.3V; VIN Rising edge detection; Package: SOT23-3			

NOTE: At present ,there are seventeen kinds of detection voltage value: 2.2V、2.4V、2.5V、2.7V、2.8V、3.0V、3.2V、3.3V、3.5V、3.6V、3.8V、3.9V、4.0V、4.2V、4.3V、4.5V、5.0V。 If you need other detection voltage and package, please contact our sales staff.

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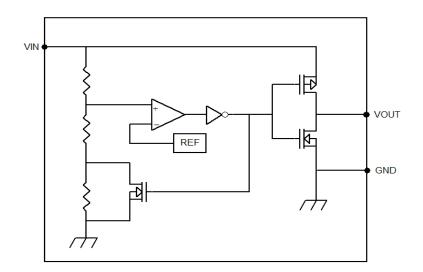
Pin Configuration



Pin Assignment

	Pin Number	Din Nome		er Pin Name Functions		Functions
SOT23	SOT23-3	TO-92	Pin Name	Functions		
2	2	3	GND	Ground		
1	1	1	V _{OUT}	Output Voltage		
3	3	2	V _{IN}	Input Voltage		

Block Diagram



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Absolute Maximum Ratings

PARAMETER		SYMBAL	RATINGS	UNITS	
V _{IN} Input Voltage		V _{INmax}	18	V	
Output Cur	rent	I _{OUTmax}	20	mA	
Output Voltage	CMOS	V _{OUT}	GND-0.3~ V _{IN} +0.3	V	
2 7.15	SOT23		0.38		
Continuous Total Power Dissipation	SOT23-3	P _D	0.54	W	
Dissipation	TO-92		0.83		
	SOT23		330		
Thermal resistance (Junction to air)	SOT23-3	SOT23-3 θ _{JA}	230	°C /W	
	TO-92		150		
Maximum junction temperature		TJ	-40~+150	$^{\circ}$	
Operating Ambient Temperature		T _{Opr}	-40~+85	$^{\circ}$ C	
Storage Temperature		T _{stg}	-55~+150	$^{\circ}$	
Soldering temperature and time		T _{solder}	260℃, 10s		

Electrical Characteristics (V_{DET} =2.0V to 7.0V , T_A =25 $^{\circ}$ C ,unless otherwise noted)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Units
Detect Voltage	V_{DET}	ME2807A V _{IN} =H-		V _{DET} ×0.99	V_{DET}	V _{DET} ×1.01	V
Hysteresis Width	V _{HYS}	$V_{IN}=L \longrightarrow H \longrightarrow L$ $V_{HYS}=V_{DET(+)}-V_{DET(-)}$	-)	V _{DET} ×0.02	V _{DET} ×0.05	V _{DET} ×0.1	V
		V _{DET} =2.0V~ 2.8V	V _{IN} =3.0V	-	1.8	4	
		V _{DET} =2.8V~ 3.6V	V _{IN} =4.0V	-	1.8	4	μΑ
Operating Current	l _{IN}	V _{DET} =3.6V~ 4.7V	V _{IN} =5.0V	-	2.1	7	
		V _{DET} =4.7V~7.0V	V _{IN} =6.0V	-	2.5	7	
Operating Voltage	V _{IN}	V _{DET} =2.0V ~ 7.0V	1	0.7	-	18	V
Output Sink Current	I _{OL}	V_{DET} =2.2V V_{DET} =2.4V V_{DET} =2.7V	V _{IN} =2V V _{OUT} =0.2V	0.5	1		mA
		V _{DET} =2.2V	V _{IN} =2.5V V _{OUT} =2.2V	-0.3	-0.5		
Output Source Current	Іон	V _{DET} =2.4V	$V_{IN} = 3V$ $V_{OUT} = 2.7V$	-0.3	-0.5		mA
		V _{DET} =2.7V	V _{IN} =3.2V V _{OUT} =2.9V	-0.3	-0.5		_
Temperature characteristics	ΔVDET/ΔTA	0°C≤Topr≤70°C			±0.9		mV/°C



Functional Description

The ME2807 series is a set of voltage detectors equipped with a high stability voltage reference which is connected to the negative input of a comparator — denoted as V_{REF} in the following figure (Fig. 1). When the voltage drop to the positive input of the comparator (i,e, V_B) is higher than V_{REF} , V_{OUT} goes high, M1 turns off, and V_B is ex-pressed as $V_{BH}=V_{IN}\times(R_B+R_C)/(R_A+R_B+R_C)$. If V_{IN} is decreased so that V_B falls to a value that is less than V_{REF} , the comparator output inverts (from high to low), V_{OUT} goes low, V_C is high, M1 turns on, R_C is bypassed, and V_B becomes: $V_{BL}=V_{IN}\times R_B/(R_A+R_B)$, which is less than V_{BH} . By so doing the comparator out-put will stay low to prevent the circuit from oscillating when $V_B \approx V_{REF}$. If V_{IN} falls bellow the minimum operating voltage, the output becomes undefined. When V_{IN} goes from low to $V_{IN}\times R_B/(R_A+R_B) > V_{REF}$, the comparator output goes high and V_{OUT} goes high again.

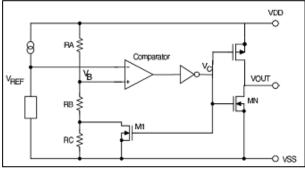


Fig.1 CMOS output voltage detector (ME2807)

ME2807A: The detection voltage is as defined:

 $V_{DET}=V_{DET(-)}=(R_A+R_B+R_C)\times V_{REF}/(R_B+R_C)$

The release voltage is as defined:

$$V_{DET(+)}=(R_A+R_B)\times V_{REF}/R_B$$

The hysteresis width is:

$$V_{HYS}=V_{DET(+)}-V_{DET(-)}$$

ME2807B: The detection voltage is as defined:

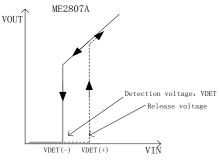
$$V_{DET}$$
= $V_{DET(+)}$ = $(R_A$ + $R_B)$ × V_{REF} / R_B

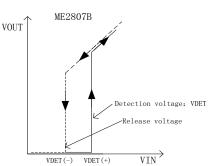
The release voltage is as defined:

$$V_{DET(-)}=(R_A+R_B+R_C)\times V_{REF}/(R_B+R_C)$$

The hysteresis width is:

$$V_{HYS} = V_{DET(+)} - V_{DET(-)}$$

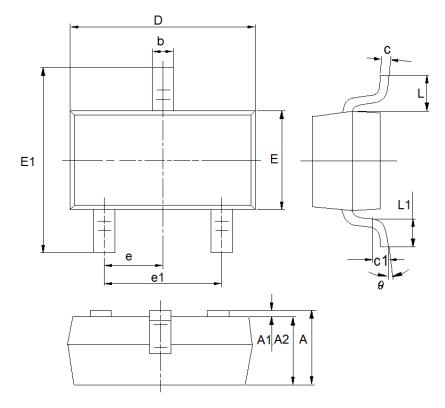






Packaging Information

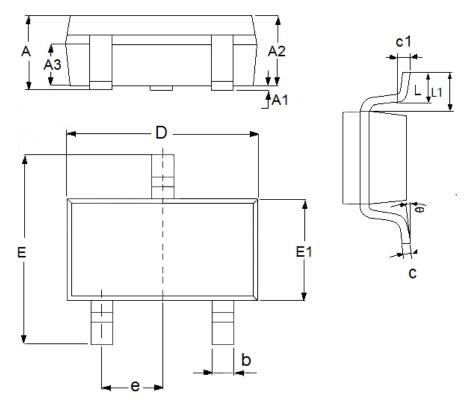
• SOT23



DIM	Millimeters		Inches	
DIN	Min	Max	Min	Max
А	0.9	1.15	0.0354	0.0453
A1	0	0.14	0.0000	0.0055
A2	0.9	1.05	0.0354	0.0413
b	0.28	0.52	0.0110	0.0205
С	0.07	0.23	0.0028	0.0091
D	2.8	3.0	0.1102	0.1181
e1	1.8	2.0	0.0709	0.0787
E	1.2	1.4	0.0472	0.0551
E1	2.2	2.6	0.0866	0.1024
е	0.95(TYP)		0.0374(TYP)	
L	0.55(TYP)		0.0217(TYP)	
L1	0.25	0.55	0.0098	0.0217
θ	0	8°	0.0000	8°
c1	0.25(TYP)		0.0098	(TYP)



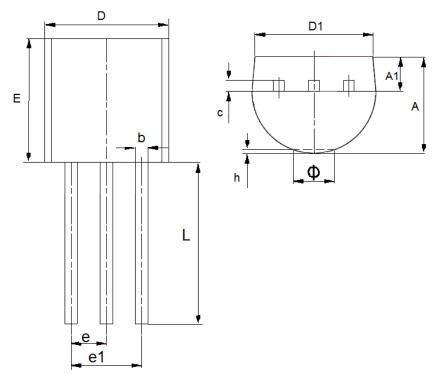
SOT23-3



DIM	Millim	eters	Inches	
DIM	Min	Max	Min	Max
Α	1.05	1.45	0.0413	0.0571
A1	0	0.15	0.0000	0.0059
A2	0.9	1.3	0.0354	0.0512
A3	0.6	0.7	0.0236	0.0276
b	0.25	0.5	0.0098	0.0197
С	0.1	0.25	0.0039	0.0098
D	2.8	3.1	0.1102	0.1220
Е	2.6	3.1	0.1023	0.1220
E1	1.5	1.8	0.0591	0.0709
е	0.95(TYP)		0.0374((TYP)
L	0.25	0.6	0.0098	0.0236
L1	0.59(TYP)		0.0232(TYP)	
θ	0	8°	0.0000	8°
c1	0.2(TYP)		0.0079((TYP)



● TO-92



DIM	Millimeters		Inc	hes
	Min	Max	Min	Max
А	3.3	3.7	0.1299	0.1457
A1	1.1	1.4	0.0433	0.0551
b	0.38	0.55	0.015	0.0217
С	0.36	0.51	0.0142	0.0201
D	4.3	4.7	0.1693	0.185
D1	3.43	_	0.135	_
E	4.3	4.7	0.1693	0.185
е	1.27TYP		0.05	TYP
e1	2.44	2.64	0.0961	0.1039
L	14.1	14.5	0.5551	0.5709
h	0	0.38	0	0.015
Ф	_	1.6	_	0.063



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